

Description

The IRLR2703TRPBF uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

D S S

TO-252-2L

General Features

 $V_{DS} = 30V I_{D} = 20A$

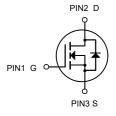
 $R_{DS(ON)}$ < 25m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRLR2703TRPBF	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (T_c=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
Vps	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	20	А
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	15	A
Ірм	Pulsed Drain Current ²	50	A
EAS	Single Pulse Avalanche Energy ³	8.1	mJ
las	Avalanche Current	12.7	A
P _D @T _C =25°C	Total Power Dissipation ⁴	20.8	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
R _θ JA	Thermal Resistance Junction-ambient ¹	62	°C/W
Rejc	Thermal Resistance Junction-Case ¹	6	°C/W



Electrical Characteristics (T_C=25 ℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V	
∆BV _{DSS} /∆T _J	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA		0.023		V/°C	
		V _{GS} =10V , I _D =10A		18	25		
Rds(on)	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =8A		25	38	mΩ	
V _{GS(th)}	Gate Threshold Voltage		1.0	1.2	2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=250uA$		-4.2		mV/°C	
I	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25°C			1	uA	
loss		V _{DS} =24V , V _{GS} =0V , T _J =55°C			5		
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =10A		5.5		S	
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		2.3		Ω	
Qg	Total Gate Charge (4.5V)			4.9		nC	
Qgs	Gate-Source Charge	V _{DS} =15V , V _{GS} =4.5V , I _D =10A		1.66			
Qgd	Gate-Drain Charge			1.85			
T _{d(on)}	Turn-On Delay Time			1.6		- ns	
Tr	Rise Time	V _{DD} =15V , V _{GS} =10V ,		15.8			
Td(off)	Turn-Off Delay Time	_R _G =3.3Ω _I _D =10A		13			
Tf	Fall Time	_ID-TOA		4.8			
Ciss	Input Capacitance			416			
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		62		pF	
Crss	Reverse Transfer Capacitance			51			
ls	Continuous Source Current ^{1,5}				24	Α	
lsм	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current			50	Α	
VsD	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V	
trr	Reverse Recovery Time	IF=10A , dI/dt=100A/μs ,		8.7		nS	
Qrr	Reverse Recovery Charge	TJ=25°C		1.95		nC	

Note:

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2The data tested by pulsed, pulse width. The EAS data shows Max. rating.

3he test condition is V $\! \leq \! 300 us$, duty cycle $_{DD=25} \! \leq \! V,\! V$ 2% $_{GS}$ =10V,L=0.1mH,I $_{AS}$ =12.7A

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

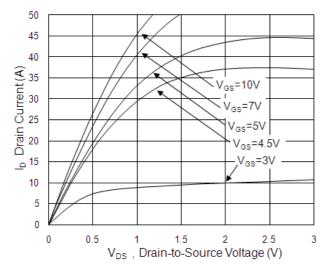


Fig.1 Typical Output Characteristics

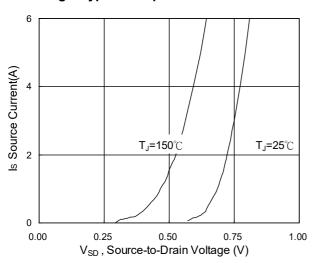


Fig.3 Forward Characteristics Of Reverse

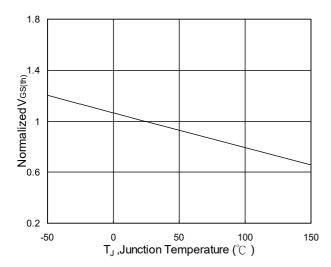


Fig.5 Normalized V_{GS(th)} vs. T_J

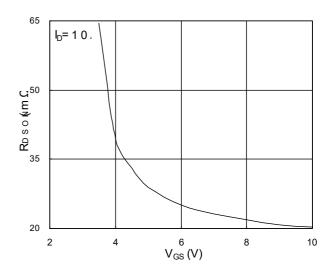


Fig.2 On-Resistance vs. Gate-Source

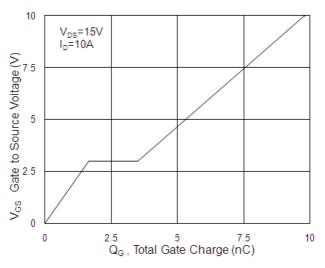


Fig.4 Gate-Charge Characteristics

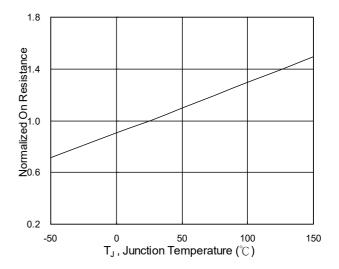
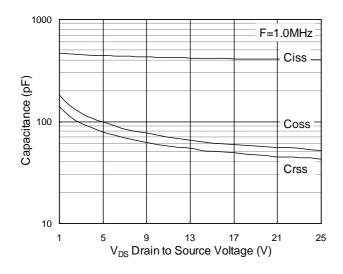


Fig.6 Normalized R_{DSON} vs. T_J



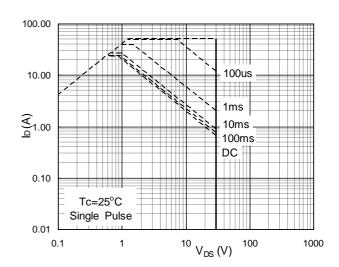


Fig.7 Capacitance

Fig.8 Safe Operating Area

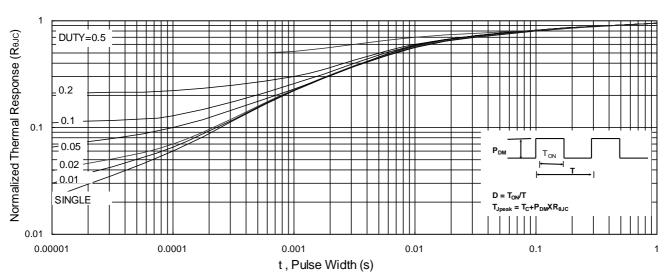


Fig.9 Normalized Maximum Transient Thermal Impedance

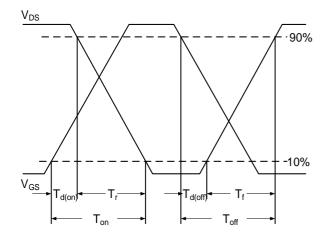


Fig.10 Switching Time Waveform

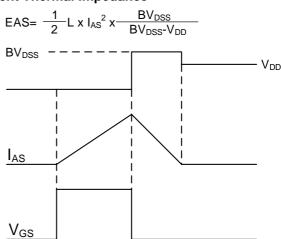
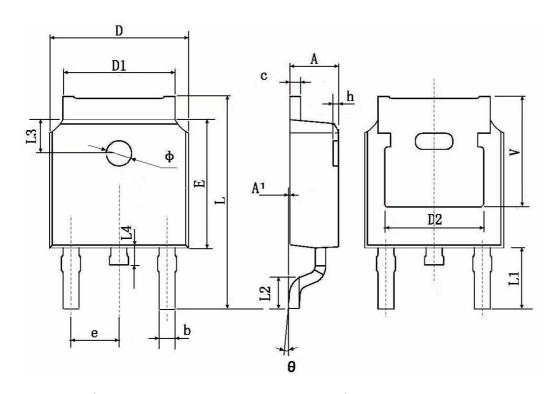


Fig.11 Unclamped Inductive Switching Waveform

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		



Attention

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production.

 HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.